

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

INOUE et al.

Serial Number: 09/473,988

Filed: December 29, 1999

For: **SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME**

AMENDMENT AFTER FINAL REJECTION

Commissioner for Patents
Washington, D.C. 20231

June 27, 2001

BOX AF

Sir:

In response to the Office Action dated February 27, 2001, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 1 and 8 as follows:

B1 rules

1. (Twice Amended) A semiconductor device comprising an insulating interlayer formed on a conductive film and including a first insulating layer of a composition containing SiH, and a second insulating layer formed on said first insulating layer,

wherein said first insulating layer has an H content of not less than 15.4 atom% in the composition, and has been formed to cover said conductive film with a third insulating layer being interposed therebetween.